

**CMHSH-3**  
**SURFACE MOUNT**  
**SILICON**  
**SCHOTTKY DIODE**

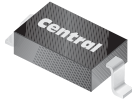


[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMHSH-3 type is a Silicon Schottky diode, epoxy molded in a SOD-123 surface mount package, designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: CH3**



**SOD-123 CASE**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
Continuous Forward Current	$I_F$	200	mA
Peak Repetitive Forward Current	$I_{FRM}$	300	mA
Peak Forward Surge Current, $t_p < 1.0\text{s}$	$I_{FSM}$	600	mA
Power Dissipation	$P_D$	400	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	312.5	$^\circ\text{C/W}$

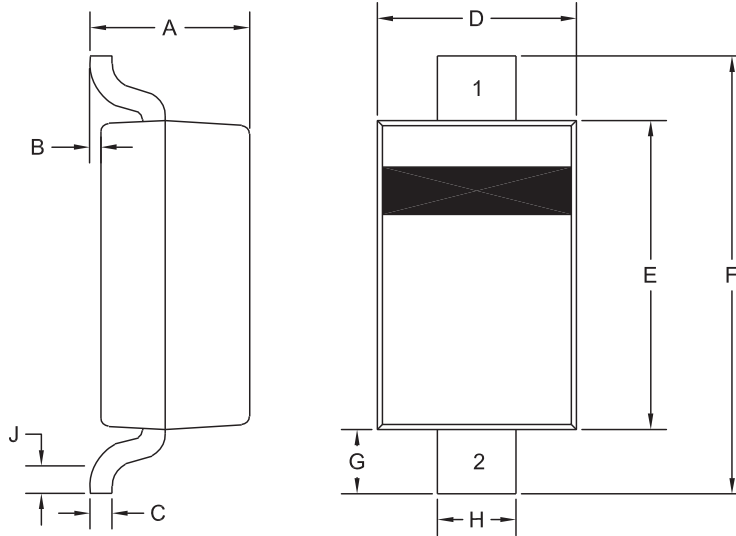
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$			2.0	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=100\mu\text{A}$			240	mV
$V_F$	$I_F=1.0\text{mA}$			320	mV
$V_F$	$I_F=10\text{mA}$			400	mV
$V_F$	$I_F=30\text{mA}$			500	mV
$V_F$	$I_F=100\text{mA}$			1000	mV
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		7.0		ns

CMHSH-3  
 SURFACE MOUNT  
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SOD-123 CASE - MECHANICAL OUTLINE



R5

LEAD CODE

- 1) Cathode
- 2) Anode

MARKING CODE: CH3

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	0.000	0.005	0.00	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.110	2.50	2.80
F	0.142	0.154	3.60	3.90
G	0.016	-	0.40	-
H	0.020	0.028	0.50	0.70
J	0.010	-	0.25	-

SOD-123 (REV:R5)

R6 (5-August 2010)